

Dual Buffer with Schmitt–Trigger Inputs

General Description

The ET74LVC2G17 is a high performance dual buffer with schmitt-trigger inputs operating from a 1.65V to 5.5V supply. This device is fabricated with advanced CMOS technology to achieve ultra-high speed with high output drive.

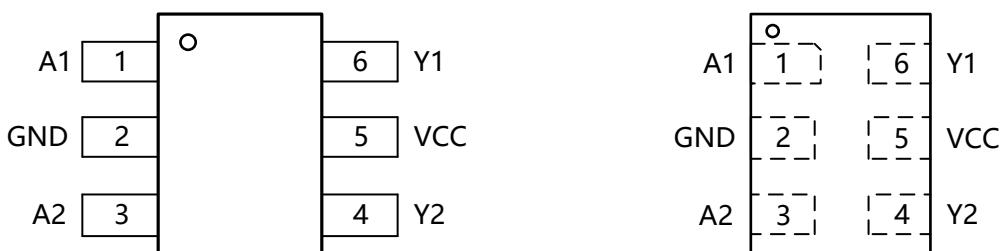
Features

- Designed for 1.65V to 5.5V VCC Operation
- Extremely High Speed $t_{PD} = 2.0\text{ns}$ (typical) at $V_{CC} = 5.0\text{V}$
- Over-Voltage Tolerant Inputs and Outputs
- 24mA Balanced Output Sink and Source Output Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- These Devices are Pb-Free and are RoHS Compliant
- Packages are SC70-6,SOT23-6 or small DFN6
- MSL1 (DFN6) , MSL3(SC70-6,SOT23-6)

Device Information

Part No.	Package	Size
ET74LVC2G17	SC70-6	1.3mm×2.1mm
ET74LVC2G17T	SOT23-6	1.6mm×2.9mm
ET74LVC2G17Y	DFN6	1.0mm×1.5mm

Pin Configuration



SC70-6/SOT23-6

DFN6(1x1.5)

Figure1. Top View

ET74LVC2G17

Pin Function

SC70-6/ SOT23-6/DFN6

Pin No.	Pin Name	Function
1	A1	Input CH1
2	GND	Ground
3	A2	Input CH2
4	Y2	Output CH2
5	VCC	Supply Voltage
6	Y1	Output CH1

Block Diagram

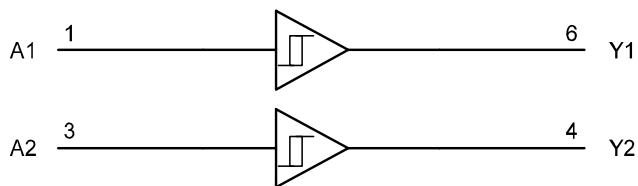


Figure2. Logic Symbol

Function Table

Input A	Output Y
L	L
H	H

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Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		-0.5 to 7.0	V
V_I	DC Input Voltage ⁽¹⁾		-0.5 ≤ V_I ≤ +7.0	V
V_O	DC Output Voltage Output in Higher or Low State		-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current $V_I < GND$		-50	mA
I_{OK}	DC Output Diode Current $V_O < GND, V_O > V_{CC}$		±50	mA
I_O	DC Output Sink Current		±50	mA
I_{O_PEAK}	DC Output Sink Pulsed Current (100μs Pulse)		±300	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Supply Pin		±100	mA
T_{STG}	Storage Temperature Range		-65 to 150	°C
T_L	Lead Temperature, Soldering 10 Seconds		260	°C
T_J	Max Junction Temperature		150	°C
V_{ESD}	ESD Classification	Human Body Model ⁽²⁾	±4000	V
		Charged Device Model ⁽³⁾	±1000	
I_{LU}	Max Latch up Current Above V_{CC} and GND at 125°C ⁽⁴⁾		±100	mA

Stresses exceeding those listed in this table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note1. IO absolute maximum rating must be observed.

Note2. Tested to EIA/JESD22-A114-A.

Note3. Tested to JESD22-C101-A.

Note4. Tested to EIA/JESD78.

Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
$R_{\theta JA}$	SC70-6	Thermal Characteristics, Thermal Resistance, Junction-to-Air	280	°C/W
	SOT23-6		180	
	DFN6(1.0×1.5)		440	
P_D	SC70-6	Power Dissipation in Still Air at 85°C	230	mW
	SOT23-6		360	
	DFN6(1.0×1.5)		150	

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Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		1.65	5.5	V
	Operating Date Retention		1.5	5.5	
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage(High or Low State)		0	5.5	V
T_A	Operating Temperature Range		-40	85	°C
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$	0	20	ns/V
		$V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$	0	10	
		$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	5	

Electrical Characteristics

DC Electrical Characteristics

Symbol	Parameter	Condition	$V_{CC}(\text{V})$	$T_A = 25 \text{ }^{\circ}\text{C}$			$-40 \text{ }^{\circ}\text{C} \leq T_A \leq 125 \text{ }^{\circ}\text{C}$		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High-Level Input Voltage		1.65 to 1.95 2.3 to 5.5	0.75 V_{CC} 0.7 V_{CC}			0.75 V_{CC} 0.7 V_{CC}		V
V_{IL}	Low-Level Input Voltage		1.65 to 1.95 2.3 to 5.5				0.25 V_{CC} 0.3 V_{CC}		V
V_{OH}	High-Level Output Voltage	$I_{OH} = -100\mu\text{A}$	1.65 to 5.5	$V_{CC} - 0.1$	V_{CC}		$V_{CC} - 0.1$		V
		$I_{OH} = -3\text{mA}$	1.65	1.29	1.52		1.29		
		$I_{OH} = -8\text{mA}$	2.3	1.9	2.1		1.9		
		$I_{OH} = -12\text{mA}$	2.7	2.2	2.4		2.2		
		$I_{OH} = -16\text{mA}$	3.0	2.4	2.7		2.4		
		$I_{OH} = -24\text{mA}$	3.0	2.3	2.5		2.3		
		$I_{OH} = -32\text{mA}$	4.5	3.8	4.0		3.8		
V_{OL}	Low-Level Output Voltage	$I_{OH} = 100\mu\text{A}$	1.65 to 5.5		0.0	0.1		0.1	V
		$I_{OL} = 3\text{mA}$	1.65		0.08	0.24		0.24	
		$I_{OL} = 8\text{mA}$	2.3		0.20	0.3		0.3	
		$I_{OL} = 12\text{mA}$	2.7		0.22	0.4		0.4	
		$I_{OL} = 16\text{mA}$	3.0		0.28	0.4		0.4	
		$I_{OL} = 24\text{mA}$	3.0		0.38	0.55		0.55	
		$I_{OL} = 32\text{mA}$	4.5		0.42	0.55		0.55	
I_{IN}	Input Leakage Current	$V_{IN} = 5.5\text{V}$ or GND	0 to 5.5	± 0.1			± 1.0		μA

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I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5V or V _{OUT} = 5.5V	0			1		10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5V or GND	5.5					10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC Electrical Characteristics

t_r = t_f = 2.5ns; C_L = 50pF; R_L = 500 Ω

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25 °C			-40°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay (Figure3 and4)	R _L = 1MΩ, C _L = 15pF	1.65	2.0	10.1	12.9	2.0	13.9	ns
			1.8	2.0	9.1	11.6	2.0	12.4	
		R _L = 1MΩ, C _L = 15pF	2.5	0.2	6.0	7.7	0.8	8.2	
		R _L = 1MΩ, C _L = 15pF	3.3	0.8	5.0	6.5	0.5	7.0	
		R _L = 500Ω, C _L = 50pF		1.2	5.6	7.1	1.5	7.6	
		R _L = 1MΩ, C _L = 15pF	5.0	0.5	4.4	5.6	0.5	6.1	
		R _L = 500Ω, C _L = 50pF		0.8	4.8	6.1	0.8	6.6	

Capacitive Characteristics

Symbol	Parameter	Condition	Typ	Unit
C _{IN}	Input Capacitance	V _{CC} = 5.5V, V _I = 0V or V _{CC}	>2.5	pF
C _{PD}	Power Dissipation Capacitance (5)	10MHz, V _{CC} = 3.3V, V _I = 0V or V _{CC}	4	pF
		10MHz, V _{CC} = 5.5V, V _I = 0V or V _{CC}	4	

Note5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)}=C_{PD}×V_{CC}×f_{in}+I_{CC}×C_{PD} is used to determine the no-load dynamic power consumption; P_D=C_{PD}×V_{CC}²×f_{in}+I_{CC}×V_{CC}×f_{ig}.

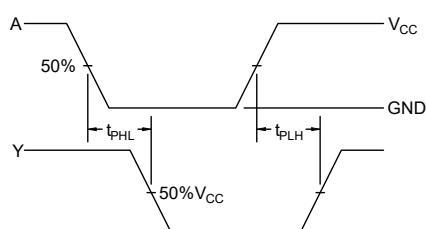


Figure 3. Switching Waveform

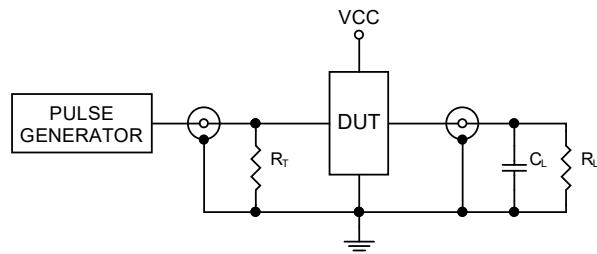
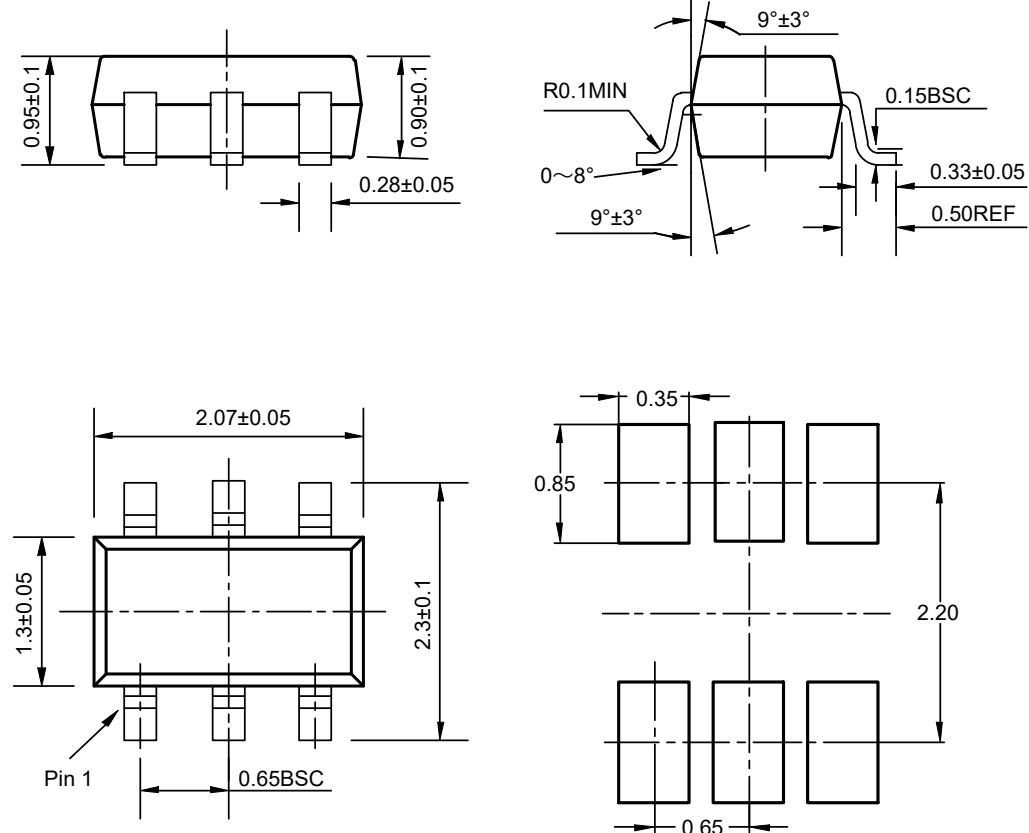


Figure4. Test Circuit

ET74LVC2G17

Package Dimension

SC70-6

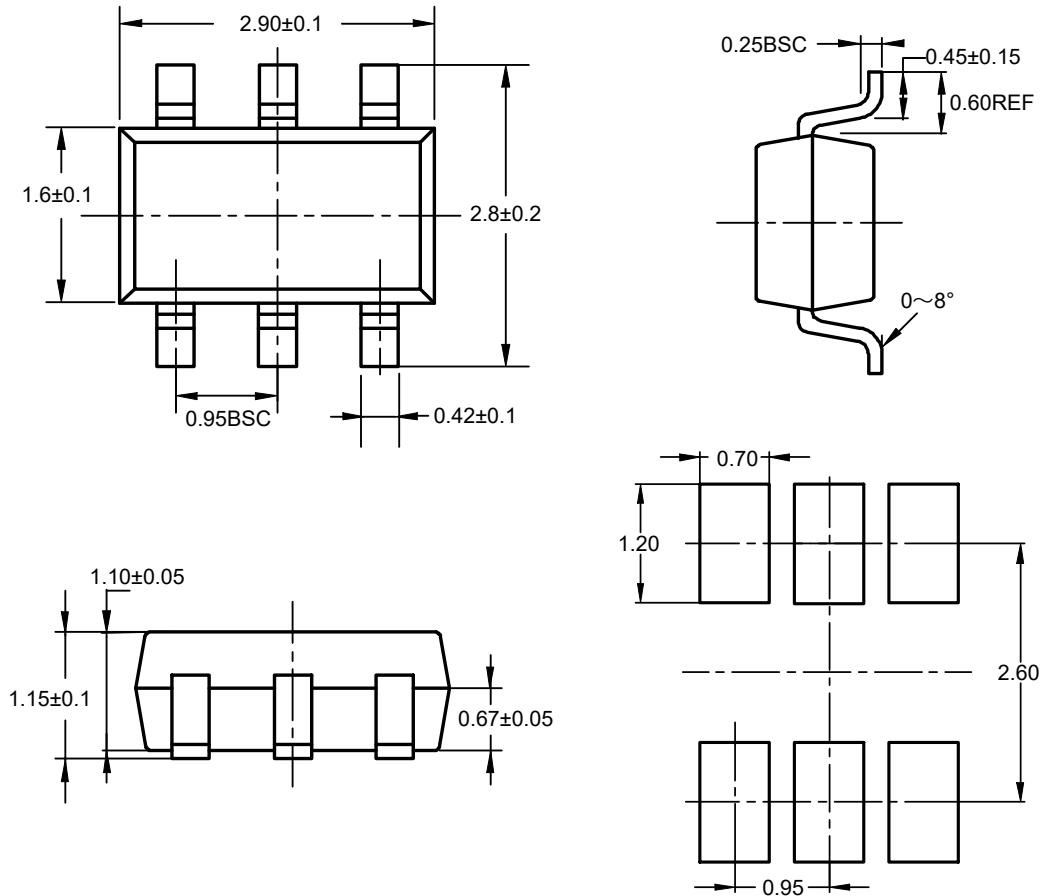


Recommended Land Pattern

Unit: mm

ET74LVC2G17

SOT23-6

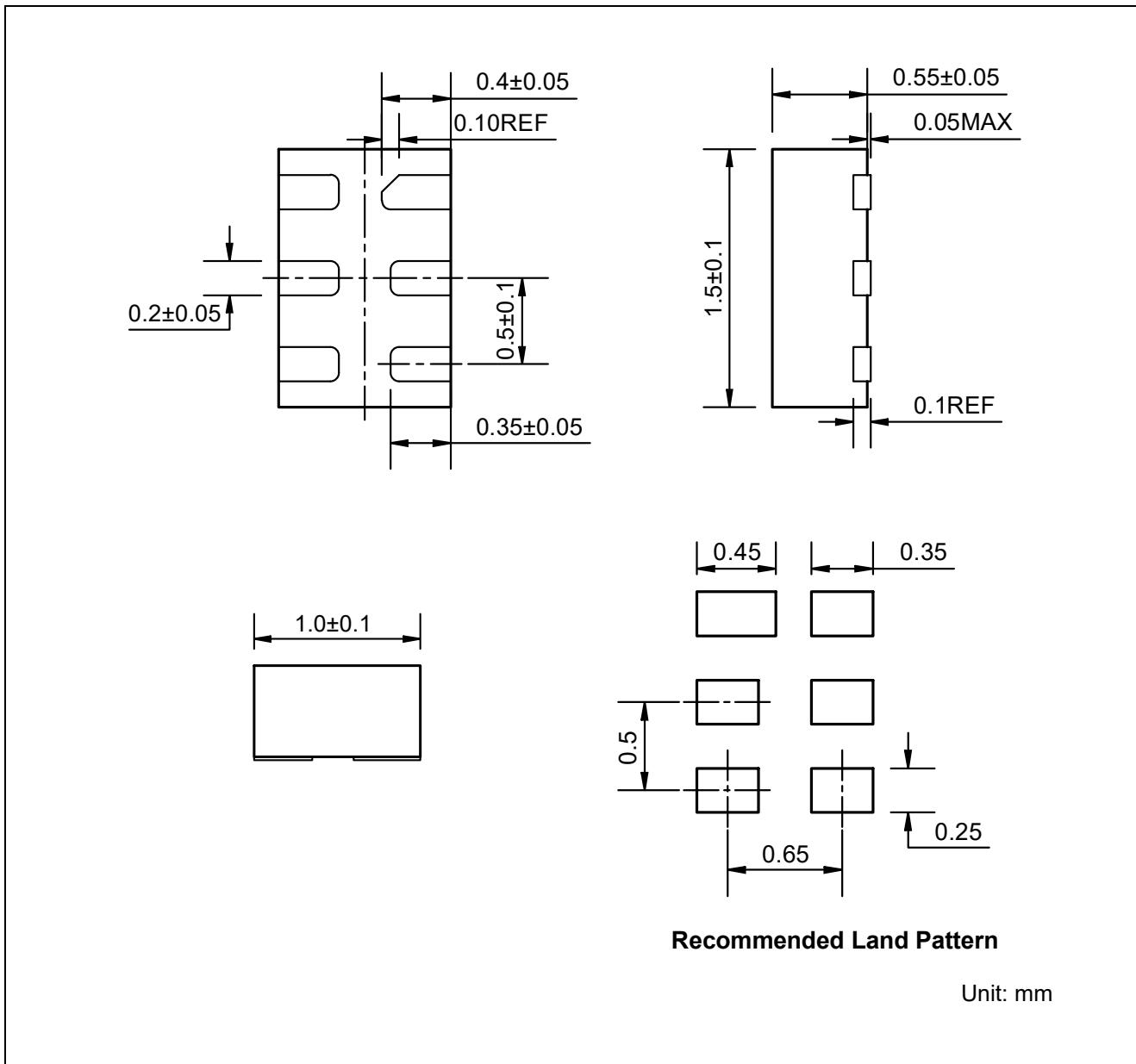


Recommended Land Pattern

Unit: mm

ET74LVC2G17

DFN6



Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2017-7-17	Original Version	Ma Yong jian	Ma Yong jian	Liu Jia Ying
1.1	2022-11-26	Update format and Thermal Characteristics	Shibo	Shibo	Shibo
1.2	2023-3-6	Add AMR DC pulsed current	Shibo	Shibo	Shibo
1.3	2023-11-29	Update package picture /ESD	Shibo	Shibo	Shibo